



Term 1449 (Modified)	Atty Docket No.	Application No.:
Information Disclosure Statement By Applicant	UNTYP017	10/612,263
(Use Several Sheets if Necessary)	Applicant:	Group
	Rinerson et al.	2818
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U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A	6,204,139	2001-03-20	Liu et al.			
	B	5,920,500	1999-07-06	Tehrani et al.			
	C	6,545,891	2003-04-08	Tringali et al.			
	D	6,504,753	2003-01-07	Scheuerlein et al.			
	E	6,483,736	2002-11-19	Johnson et al.			
	F	6,385,074	2002-05-07	Johnson et al.			
	G	6,351,406	2002-02-26	Johnson et al.			
	H	6,185,122	2001-02-06	Johnson et al.			
	I	6,034,882	2000-03-07	Johnson et al.			
	J	5,835,396	1998-11-10	Zhang			
	K	4,442,507	1994-04-10	Roesner			

U.S. Published Patent Applications

Examiner Initial	No.	Document No.	Publication Date	Inventor
Don	J	2002/0000597 A1	01/03/02	Okazawa
Don	K	2001/0023992 A1	09/27/01	Doll

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>Dr</i>	L	Beck, A. et al., "Reproducible switching effect in thin oxide films for memory applications", Applied Physics Letters, Vol. 77, No. 1, 3 July 2000, 139-141.
	M	Rossel, C. et al., "Electrical current distribution across a metal-insulator-metal structure during bistable switching", Journal of Applied Physics, Vol. 90, No. 6, 15 September 2001, 2892-2898.
<i>Dr</i>	N	Watanabe, Y. et al., "Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped $SrTiO_3$ single crystals", Applied Physics Letters, Vol. 78, No. 23, 4 June 2001, 3738-3740.

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Form 1449 (Modified)

Information Disclosure
Statement By Applicant

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Rinerson et al.
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July 1, 2003

Group
2824

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>Du</i>	A	Liu, S.Q., et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", Applied Physics Letters, Vol. 76, No. 19, 8 May 2000, 2749-2651.
<i>Du</i>	B	Liu, S.Q., et al., "A New Concept For Non-Volatile Memory: Electric-Pulse Induced Reversible Resistance Change Effect In Magnetoresistive Films", Space Vacuum Epitaxy Center, University of Huston, Huston TX, 7 Pages.
Examiner	Date Considered <i>TUAN T. NGUYEN</i> 2/7/05	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.